

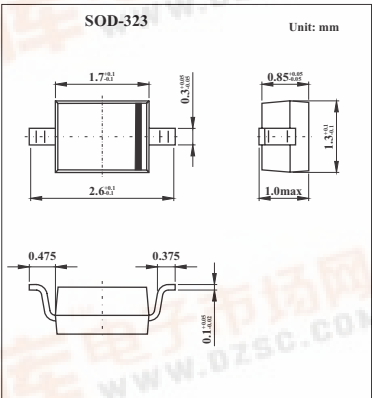
SMD Type

Diodes

SURFACE MOUNT SCHOTTKY BARRIER DIODE
SD101AWS

Features

- Low Forward Voltage Drop
- Guard Ring Construction for Transient Protection
- Negligible Reverse Recovery Time
- Low Capacitance
- Ultra-small Surface Mount Package



Absolute Maximum Ratings $T_a = 25^{\circ}\text{C}$

Paramater	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}		
Working Peak Reverse Voltage	V_{RWM}	60	V
DC Blocking Volatge	V_R		
RMS Reverse Voltage	$V_{R(RMS)}$	40	V
Forward Continuous Current (Note 1)	I_{FM}	15	mA
Non-Repetitive Peak Forward Surge Current @ $t \leq 1.0\text{s}$ @ $t = 10 \mu\text{s}$	I_{FSM}	50 2.0	mA A
Power Dissipation (Note1)	P_d	200	mW
Thermal Resistance, Junction to Ambient Air (Note 1)	$R_{\theta JA}$	625	$^{\circ}\text{C}/\text{W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-65 to +125	$^{\circ}\text{C}$

Note:

1. Part mounted on FR-4 PC borad with recommended pad layout.

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■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Characteristic	Symbol	Test Condition	Min	Max	Unit
Reverse Breakdown Voltage (Note 2)	$V_{(BR)R}$	$V_R = 10\ \mu\text{A}$	60		V
Forward Voltage Drop (Note 2)	V_{FM}	$I_F = 1.0\text{ mA}$		0.41	V
		$I_F = 15\text{ mA}$		1.00	
Peak Reverse Leakage Current (Note 2)	I_{RM}	$V_R = 50\text{ V}$		200	μA
Total Capacitance	C_T	$V_R = 0\text{ V}$, $f = 1.0\text{ MHz}$		2.0	pF
Reverse Recovery Time	t_{rr}	$I_F = I_R = 5.0\text{ mA}$ $I_{rr} = 0.1 \times I_R$, $R_L = 100\ \Omega$		1.0	ns

Note:

2. Short duration test pulse used to minimize self-heating effect.

■ Marking

Marking	S1
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